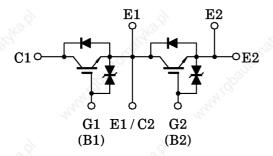
TOSHIBA GTR Module Silicon N Channel IGBT

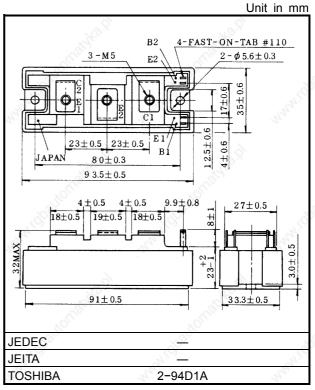
## MG50Q2YS40

# High Power Switching Applications. Motor Control Applications.

- High input impedance
- High speed:  $tf = 0.5\mu s$  (max.)  $trr = 0.5\mu s$  (max.)
- Low saturation voltage
  - $V_{CE(sat)} = 4.0 V \text{ (max.)}$
- Enhancement-mode
- Includes a complete half bridge in one package.
- The electrodes are isolated from case.

#### **Equivalent Circuit**





Weight: 202g

#### **Maximum Ratings (Ta = 25°C)**

	2,175		4.77		
Characteristic  Collector–emitter voltage  Gate–emitter voltage		Symbol	Rating	Unit	
		V <sub>CES</sub>	1200	V	
		V <sub>GES</sub>	±20		
Collector current	DC	, Ic	50	A	
	1ms	I <sub>CP</sub>	100		
Forward current	DC	lF	50	- A	
	1ms	I <sub>FM</sub>	100		
Collector power dissipation (Tc = 25°C)		PC	400	W	
Junction temperature		Tjo	150	°C	
Storage temperature range		T <sub>stg</sub>	-40~125	°C	
Isolation voltage		V <sub>Isol</sub>	2500 (AC 1 minute)	V	
Screw torque (terminal / mounting)		_	3/3	N∙m	

### Electrical Characteristics (Ta = 25°C)

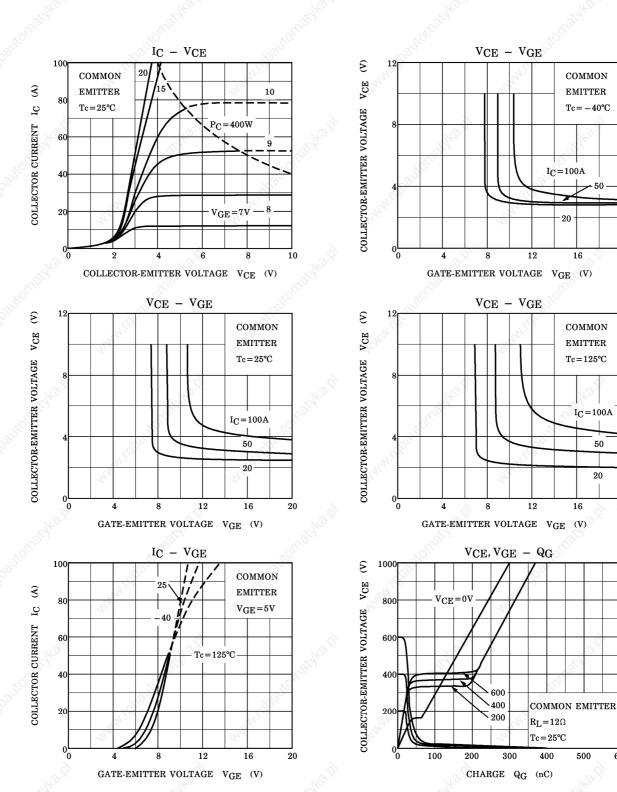
	720				720		
Characteristic		Symbol	Test Condition	Min.	Тур.	Max.	Unit
Gate leakage current		I <sub>GES</sub>	V <sub>GE</sub> = ±20V, V <sub>CE</sub> = 0	77	_	±10	μA
Collector cut-off current		I <sub>CES</sub>	V <sub>CE</sub> = 1200V, V <sub>GE</sub> = 0	_	_	1.0	mA
Gate-emitter cut-off voltage		V <sub>GE(off)</sub>	I <sub>C</sub> = 50mA, V <sub>CE</sub> = 5V	3.0	_	6.0	V
Collector–emitter saturation voltage	· Jourgian	V <sub>CE(sat)</sub>	I <sub>C</sub> = 50A, V <sub>GE</sub> = 15V	-	3.0	4.0	V
Input capacitance		C <sub>ies</sub>	V <sub>CE</sub> = 10V, V <sub>GE</sub> = 0, f = 1MHz	141.0°	6000	_	pF
Switching time	Rise time	$\mathcal{L}^{\mathcal{L}}$ $t_{r}$		200	0.3	0.6	μs
	Turn-on time	t <sub>on</sub>		_	0.4	0.8	
	Fall time	t <sub>f</sub>		_	0.2	0.5	
	Turn-off time	t <sub>off</sub>	= 15V	_	0.8	1.5	
Forward voltage		VF	I <sub>F</sub> = 50A, V <sub>GE</sub> = 0	- 5	2.0	2.5	V
Reverse recovery time		trr	I <sub>F</sub> = 50A, V <sub>GE</sub> = -10V di / dt = 100A / µs	14 4 10.	0.25	0.5	μs
Thermal resistance F		D.,	Transistor	_	_	0.31	°C/W
		R <sub>th(j-c)</sub>	Diode	_	_	1.0	] C/W

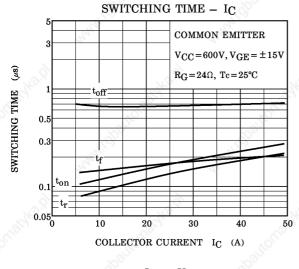
20

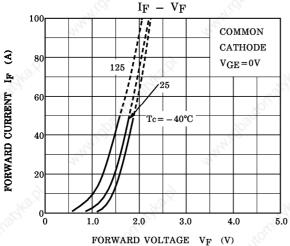
VGE

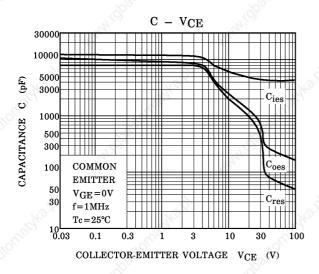
GATE-EMITTER VOLTAGE

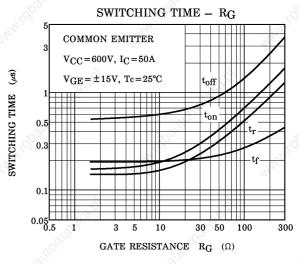
600

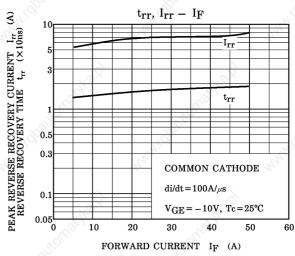


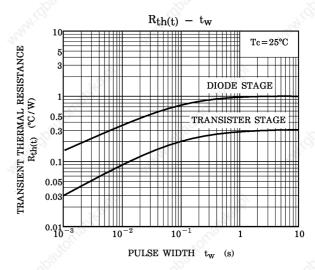


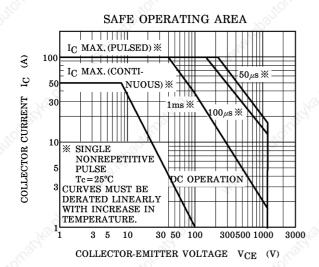


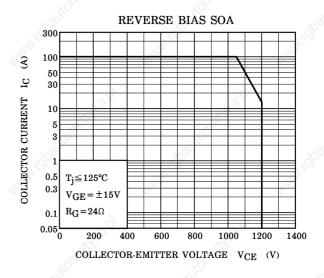












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